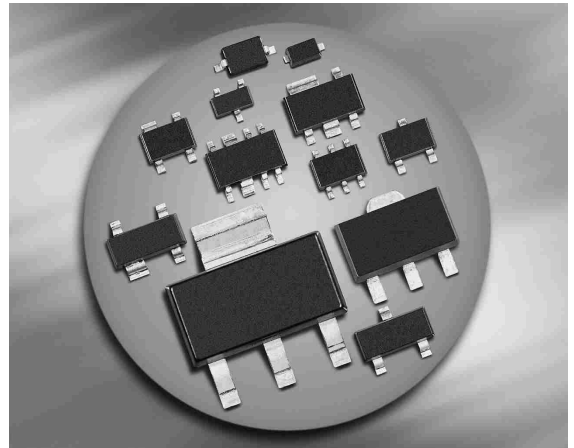
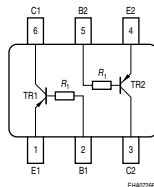
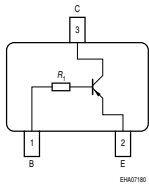


PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit.
- Built in bias resistor ($R_1 = 10\text{k}\Omega$)
- For 6-PIN packages: two (galvanic) internal isolated transistors with good matching in one package



BCR179F/L3 **SEMB4**
BCR179T



Type	Marking	Pin Configuration						Package
BCR179F	WWs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR179L3	WW	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR179T	WWs	1=B	2=E	3=C	-	-	-	SC75
SEMB4	WW	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT666

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Input on voltage	$V_{I(on)}$	20	
Collector current	I_C	100	mA
Total power dissipation	P_{tot}		mW
BCR179F, $T_S \leq 128^\circ\text{C}$		250	
BCR179L3, $T_S \leq 135^\circ\text{C}$		250	
BCR179T, $T_S \leq 109^\circ\text{C}$		250	
SEMB4, $T_S \leq 75^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	150 ... -65	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR179F		≤ 90	
BCR179L3		≤ 60	
BCR179T		≤ 109	
SEMB4		≤ 300	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

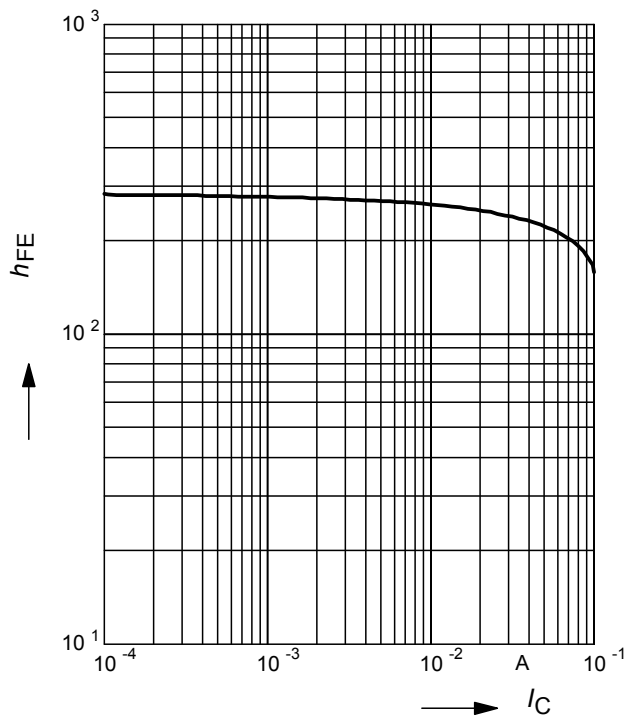
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$, $I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}$, $I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Emitter-base breakdown voltage $I_E = 10\ \mu\text{A}$, $I_C = 0$	$V_{(\text{BR})\text{EBO}}$	5	-	-	
Collector-base cutoff current $V_{\text{CB}} = 40\ \text{V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 5\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$	h_{FE}	120	-	630	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\ \text{mA}$, $I_B = 0,5\ \text{mA}$	V_{CEsat}	-	-	0,3	V
Input off voltage $I_C = 100\ \mu\text{A}$, $V_{\text{CE}} = 5\ \text{V}$	$V_{\text{i(off)}}$	0,4	-	1	
Input on voltage $I_C = 2\ \text{mA}$, $V_{\text{CE}} = 0,3\ \text{V}$	$V_{\text{i(on)}}$	0,5	-	1,1	
Input resistor	R_1	7	10	13	kΩ
AC Characteristics					
Transition frequency $I_C = 10\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$, $f = 100\ \text{MHz}$	f_{T}	-	150	-	MHz
Collector-base capacitance $V_{\text{CB}} = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_{cb}	-	1,2	-	pF

¹⁾Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

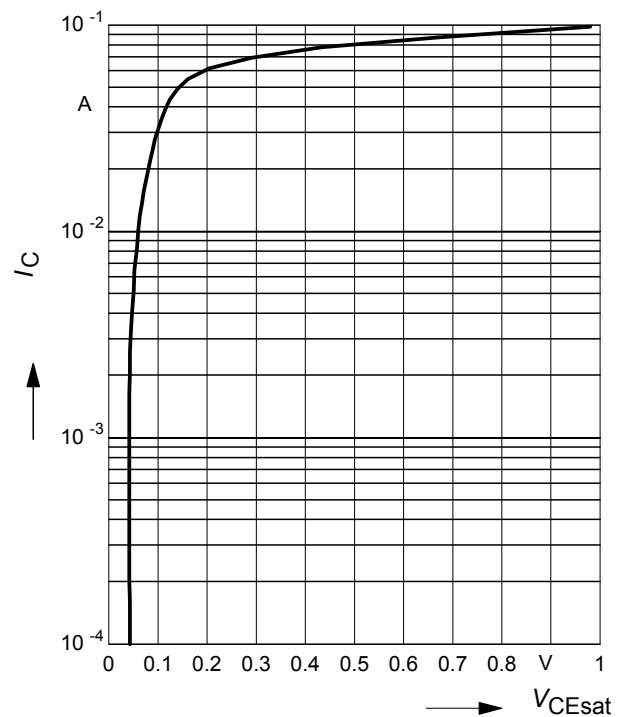
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



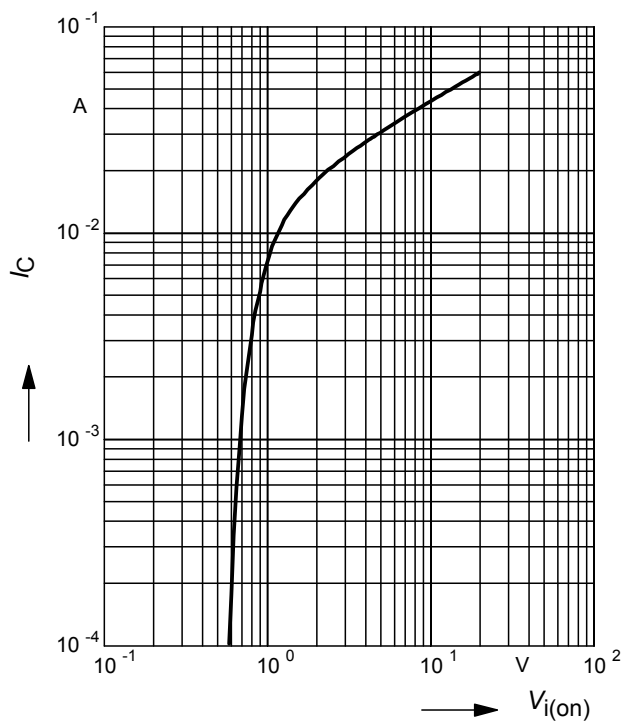
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



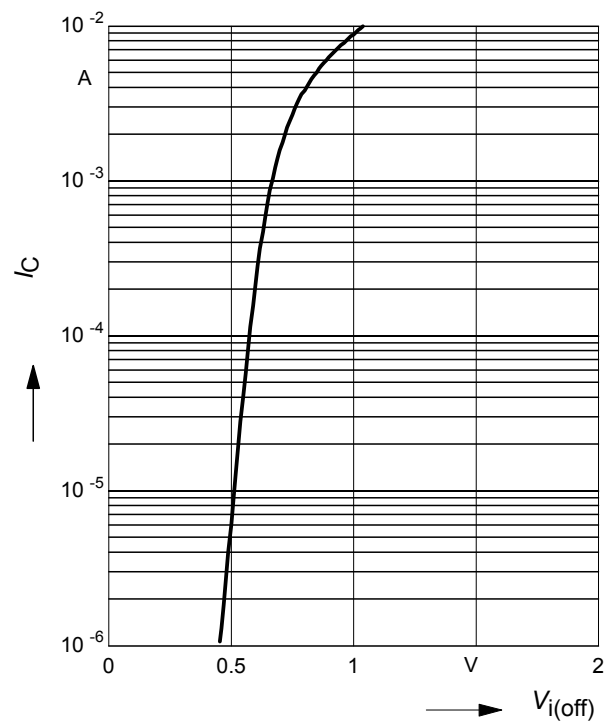
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3 \text{ V}$ (common emitter configuration)



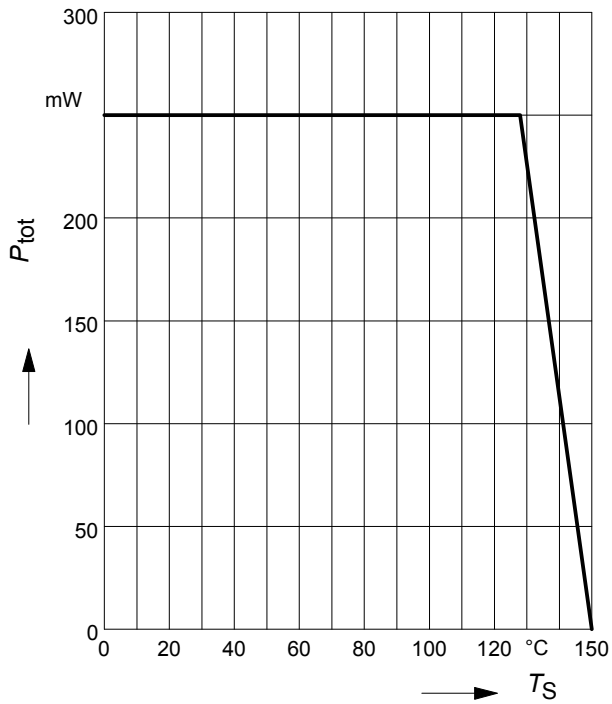
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



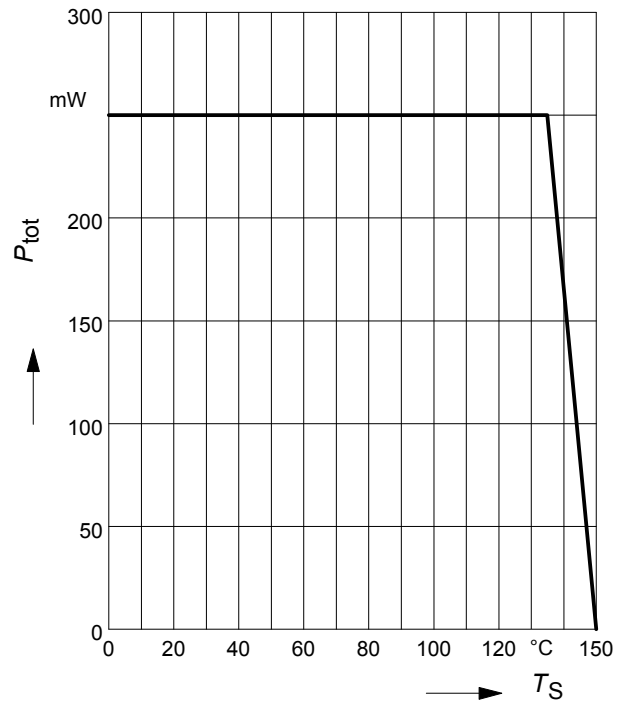
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR179F



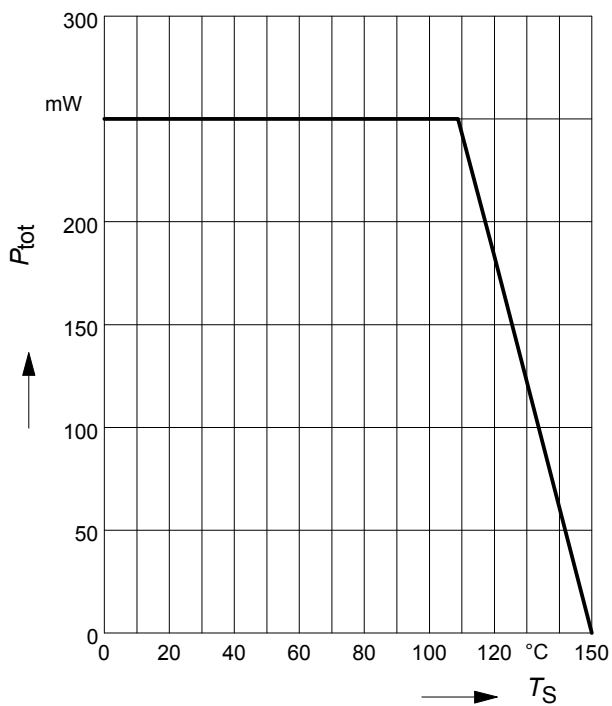
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR179L3



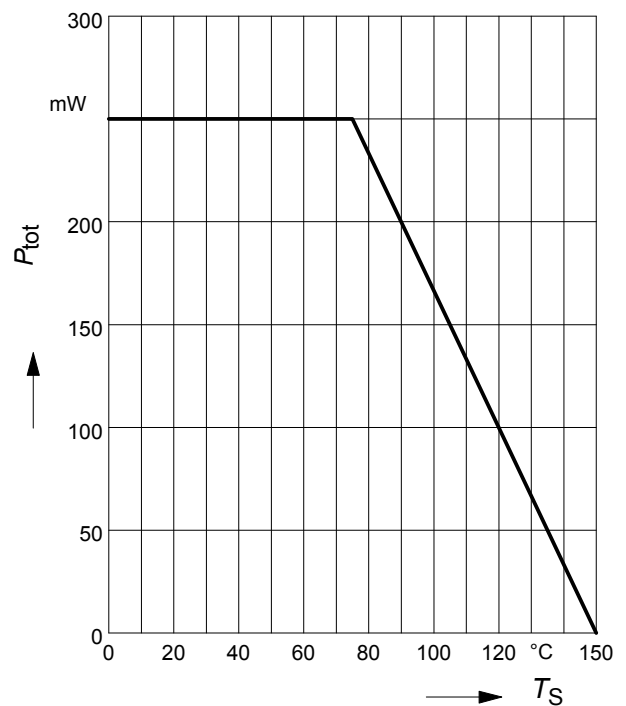
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR179T



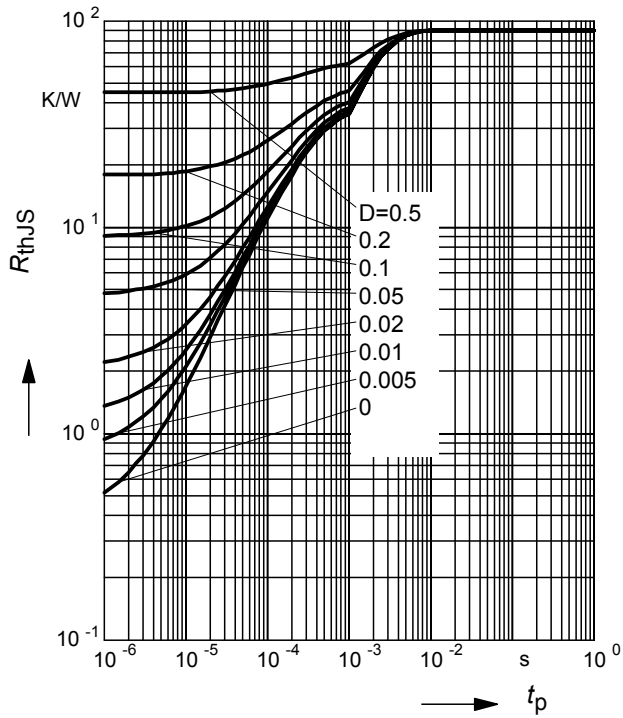
Total power dissipation $P_{\text{tot}} = f(T_S)$

SEMB4



Permissible Puls Load $R_{thJS} = f(t_p)$

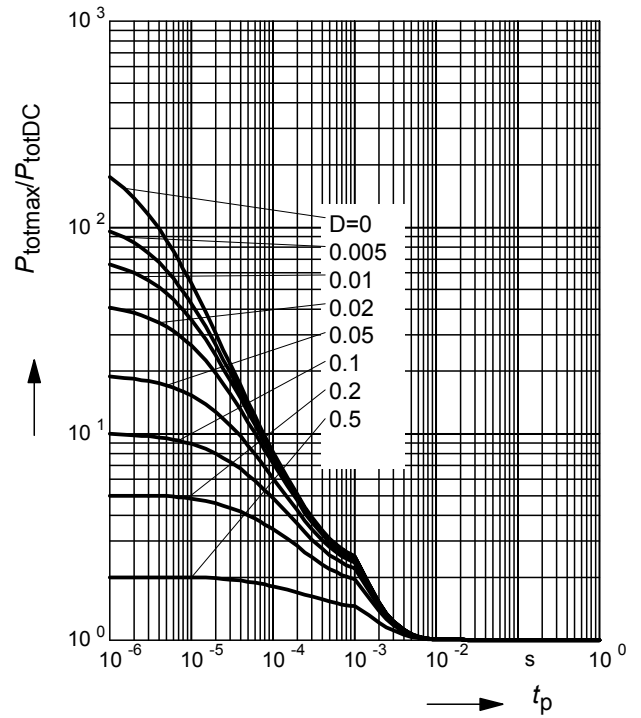
BCR179F



Permissible Pulse Load

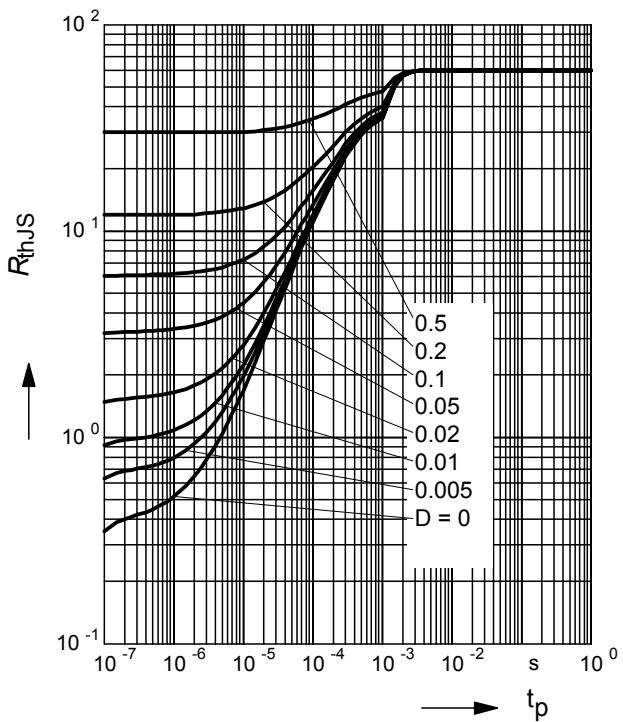
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR179F



Permissible Puls Load $R_{thJS} = f(t_p)$

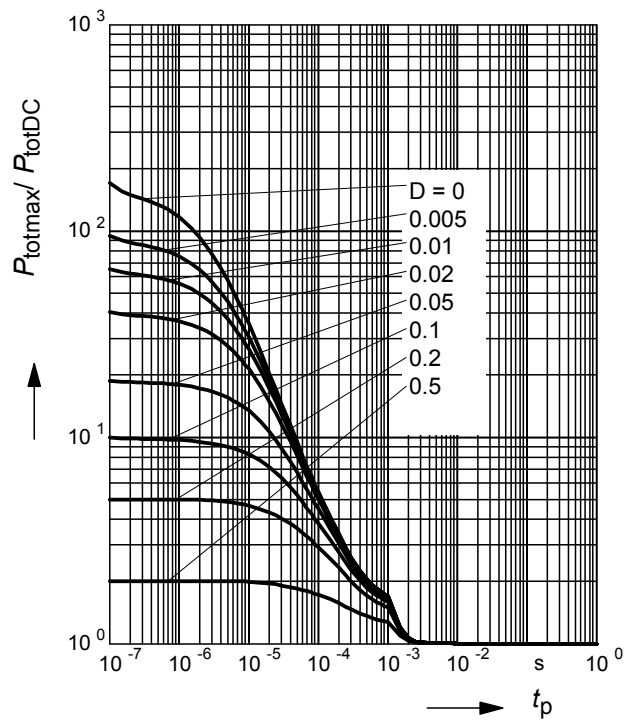
BCR179L3



Permissible Pulse Load

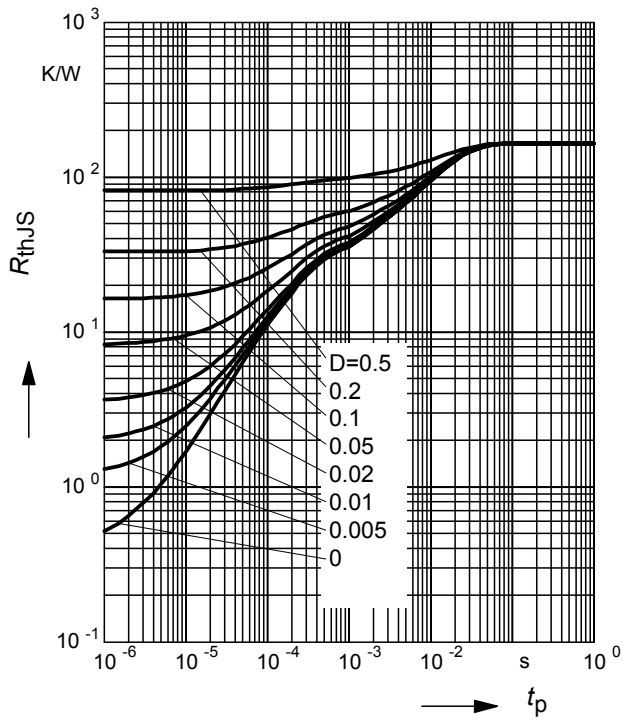
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR179L3



Permissible Puls Load $R_{thJS} = f(t_p)$

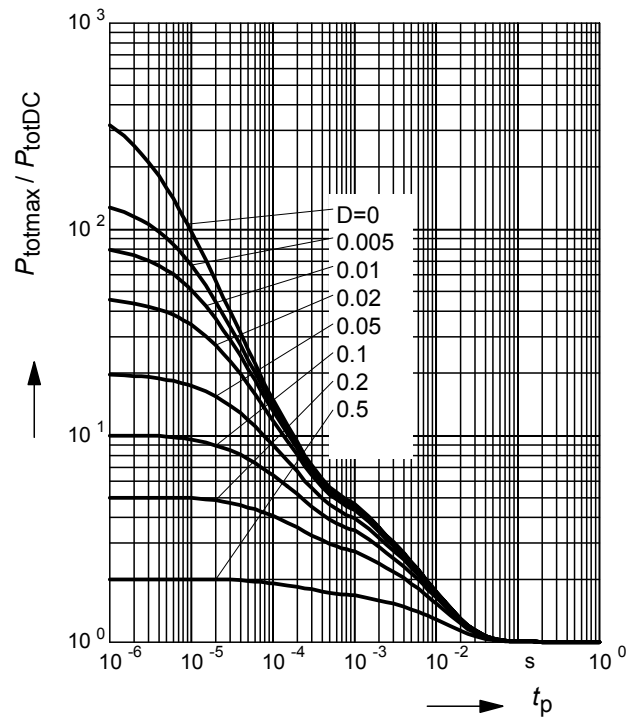
BCR179T



Permissible Pulse Load

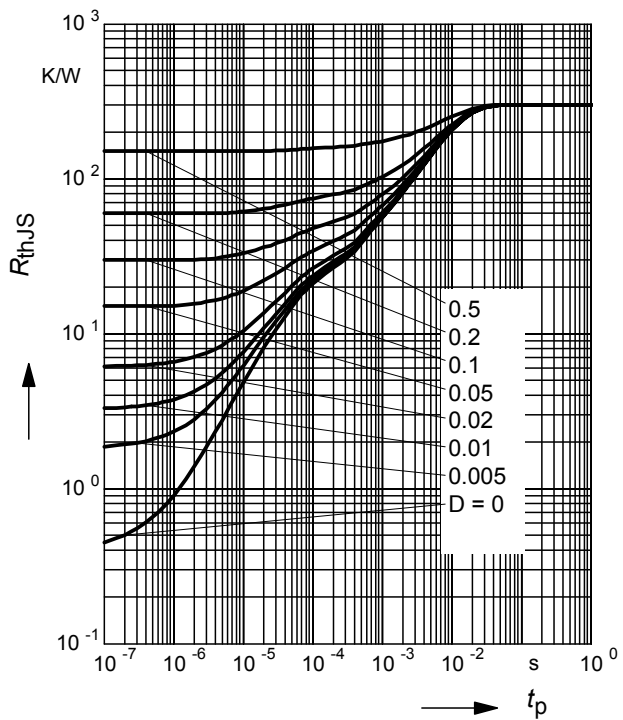
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR179T



Permissible Puls Load $R_{thJS} = f(t_p)$

SEMB4



Permissible Pulse Load

$$P_{totmax}/P_{totDC} = f(t_p)$$

SEMB4

